1	Search Text	DB	Time stamp
72524	tan/tantalum adi3 nitride)	HSDAT:	2003/03/25
12324	tan(tantalum adjo nittide)		12:23
		EPO; JPO;	12.20
		DERWENT;	1
		IBM TDB	1
72524	tan (tantalum adj3 nitride)	USPAT;	2003/03/25
		US-PGPUB;	12:23
1			
			0000/00/05
3889			2003/03/25
	nitride)))		12:24
)
4074	(conformal diffussion diffused barrier)		2003/03/25
10,1	, , , , , , , , , , , , , , , , , , , ,	US-PGPUB;	12:25
	, , , , , , , , , , , , , , , , , , , ,	EPO; JPO;	
		DERWENT;	
		IBM_TDB	1
2281	((conformal diffussion diffused barrier)	USPAT;	2003/03/25
	with (ta (tan (tantalum adj3 nitride))))	US-PGPUB;	12:26
	same (copper cu)		1
1774	(()		2002/02/25
1//4	, , ,		2003/03/25
		i ·	12.20
			1
	CIICALE, IC,	IBM TDB	
	3889 4074	tan (tantalum adj3 nitride) 3889 barrier with (ta (tan (tantalum adj3 nitride))) 4074 (conformal diffussion diffused barrier) with (ta (tan (tantalum adj3 nitride))) 2281 ((conformal diffussion diffused barrier) with (ta (tan (tantalum adj3 nitride)))) same (copper cu)	T2524 tan (tantalum adj3 nitride) T2525 tan (tantalum adj3 nitride) T2526 tan (tantalum adj3 nitride) T2527 tantalum adj3 nitride) T2528 tan (tantalum adj3 nitride) T2529 tantalum adj3 nitride) T2529 tantalum adj3 nitride) T2520 tantalum adj3 nitride)

ELECTROCHEMICAL TRENCH COPPER INSULATE SEED BARRIER LAYER

DERWENT-CLASS: L03 U11

CPI-CODES: L04-C10D;

EPI-CODES: U11-C05C6; U11-D03B2;

SECONDARY-ACC-NO:

CPI Secondary Accession Numbers: C2000-142190 Non-CPI Secondary Accession Numbers: N2000-354197

03/25/2003, EAST Version: 1.03.0002